

PNP General Purpose Transistor

MMBTA55/A56

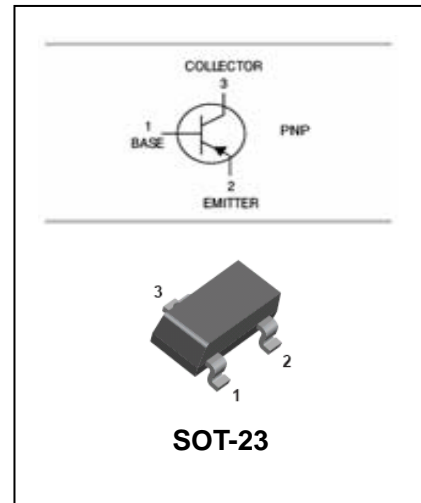
FEATURES

- Epitaxial planar die construction.
- Complementary NPN types available (MMBTA05/MMBTA06).



APPLICATIONS

- Ideal for medium NPN amplification and switching.



ORDERING INFORMATION

Type No.	Marking	Package Code
MMBTA55	2H	SOT-23
MMBTA56	2GM	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	MMBTA55	MMBTA56	UNIT
V_{CBO}	collector-base voltage	-60	-80	V
V_{CEO}	collector-emitter voltage	-60	-80	V
V_{EBO}	emitter-base voltage	-4		V
I_C	collector current (DC)	-0.5		A
P_C	Collector dissipation	0.3		W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	417		°C/W
T_J, T_{stg}	junction and storage temperature	-55 to +150		°C



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage MMBTA55 MMBTA56	$I_C = -100\mu A, I_E = 0$	-60 -80		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage MMBTA55 MMBTA56	$I_C = -1.0mA, I_B = 0$	-60 -80		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-4		V
I_{CBO}	Collector cut-off current MMBTA55 MMBTA56	$I_E = 0; V_{CB} = -60V$ $I_E = 0; V_{CB} = -80V$	-	-0.1	μA
I_{CEO}	Collector cut-off current MMBTA55 MMBTA56	$I_B = 0; V_{CB} = -60V$ $I_B = 0; V_{CB} = -80V$	-	-0.1	μA
h_{FE}	DC current gain	$V_{CE} = -1V; I_C = -10mA$ $V_{CE} = -1V; I_C = -100mA$	100 100	- -	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -100mA; I_B = -10mA$	-	-0.25	V
$V_{BE(on)}$	Base-emitter saturation voltage	$I_C = -100mA; V_{CE} = -1.0V$	-	-1.2	V
f_T	transition frequency	$I_C = -100mA; V_{CE} = -1V;$ $f = 100MHz$	50	-	MHz

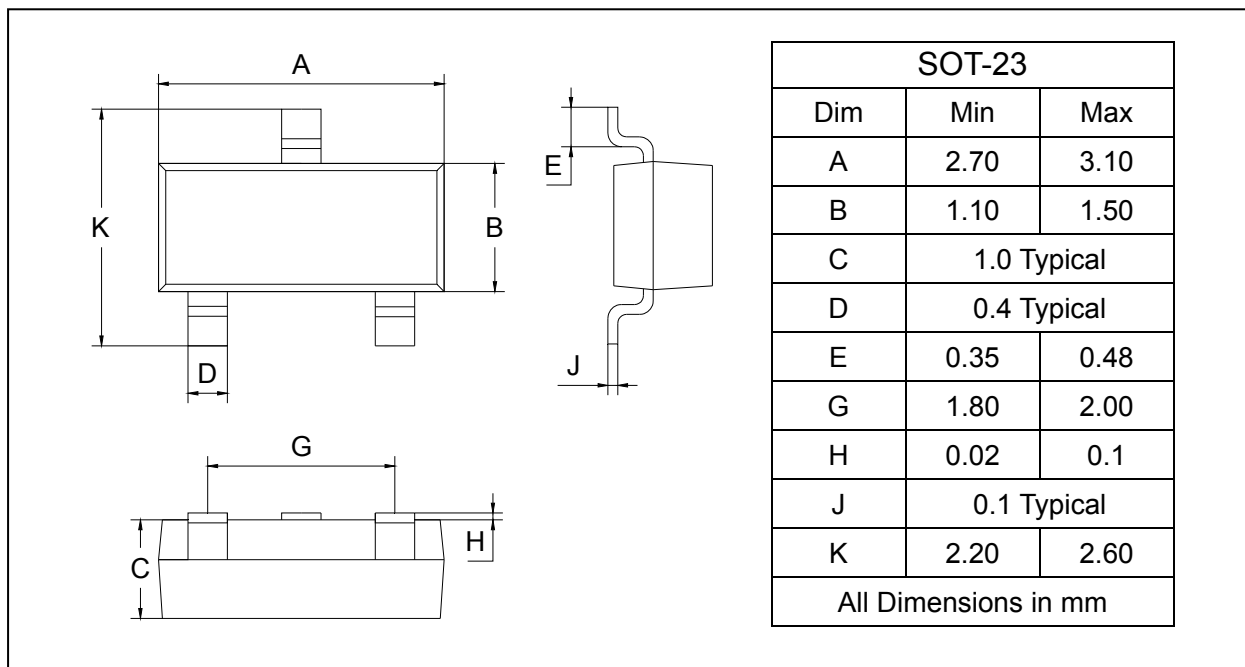
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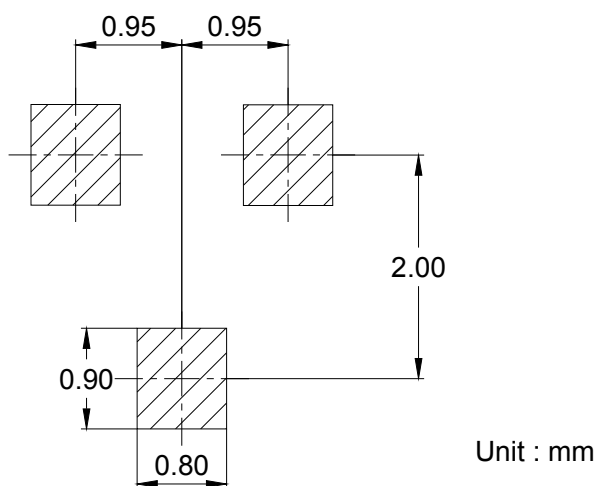
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMBTA55/MMBTA56	SOT-23	3000/Tape&Reel